

High Voltage Standard Rectifier

$$V_{RRM} = 2200 \text{ V}$$

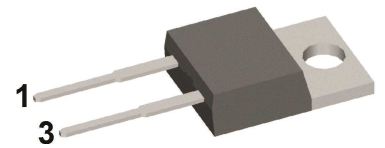
$$I_{FAV} = 30 \text{ A}$$

$$V_F = 1.24 \text{ V}$$

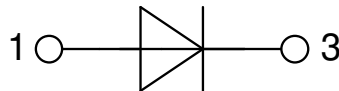
Single Diode

Part number

DNA30E2200PA



Backside: anode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					2300	V
V_{RRM}	max. repetitive reverse blocking voltage					2200	V
I_R	reverse current	$V_R = 2200$ V		$T_{VJ} = 25^\circ\text{C}$		40	μA
		$V_R = 2200$ V		$T_{VJ} = 150^\circ\text{C}$		1.5	mA
V_F	forward voltage drop	$I_F = 30$ A		$T_{VJ} = 25^\circ\text{C}$		1.26	V
		$I_F = 60$ A				1.53	V
		$I_F = 30$ A		$T_{VJ} = 150^\circ\text{C}$		1.24	V
		$I_F = 60$ A				1.63	V
I_{FAV}	average forward current	$T_C = 140^\circ\text{C}$		$T_{VJ} = 175^\circ\text{C}$		30	A
		rectangular	d = 0.5				
V_{FO}	threshold voltage			$T_{VJ} = 175^\circ\text{C}$		0.83	V
r_F	slope resistance					13.4	m Ω
						} for power loss calculation only	
R_{thJC}	thermal resistance junction to case					0.7	K/W
R_{thCH}	thermal resistance case to heatsink				0.5		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		210	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		370	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		400	A
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		315	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		340	A
I^2t	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		685	A ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		665	A ² s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		495	A ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		480	A ² s
C_J	junction capacitance	$V_R = 700$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		7	pF



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Part description

- D = Diode
- N = High Voltage Standard Rectifier
- A = (>= 2000V)
- 30 = Current Rating [A]
- E = Single Diode
- 2200 = Reverse Voltage [V]
- PA = TO-220AC (2)

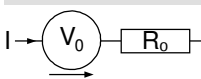
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DNA30E2200PA	DNA30E2200PA	Tube	50	507762

Similar Part	Package	Voltage class
DNA30E2200PZ	TO-263AB (D2Pak) (2HV)	2200
DNA30EM2200PZ	TO-263AB (D2Pak) (2HV)	2200
DNA30E2200FE	i4-Pac (2HV)	2200
DNA30E2200IY	TO-262 (2HV) (I2PAK)	2200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 175^{\circ}C$

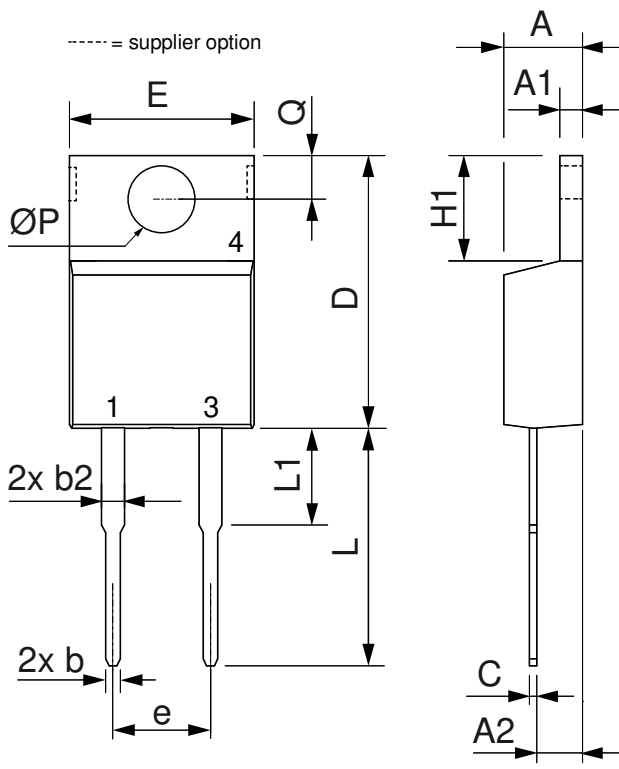


Rectifier

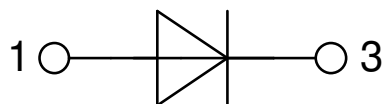
$V_{0\ max}$	threshold voltage	0.83	V
$R_{0\ max}$	slope resistance *	10.2	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



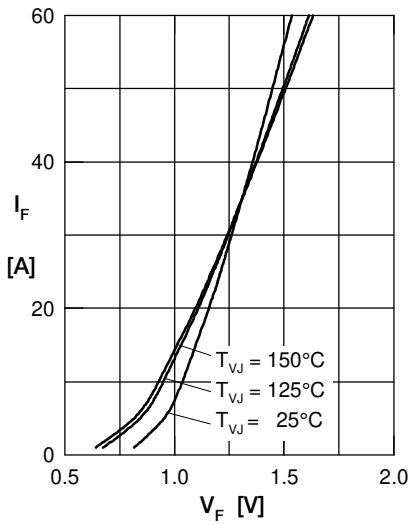
Rectifier


Fig. 1 Forward current versus voltage drop per diode

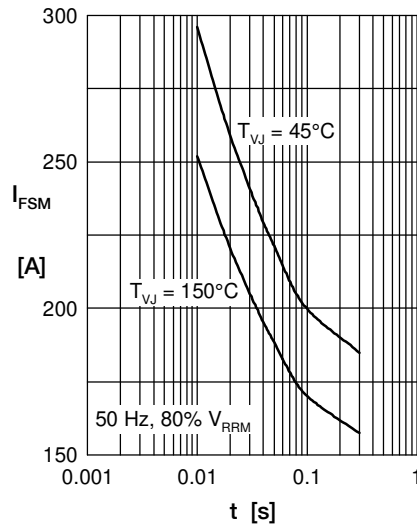


Fig. 2 Surge overload current

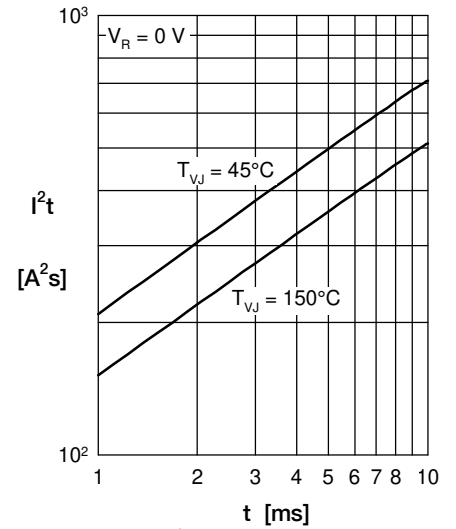
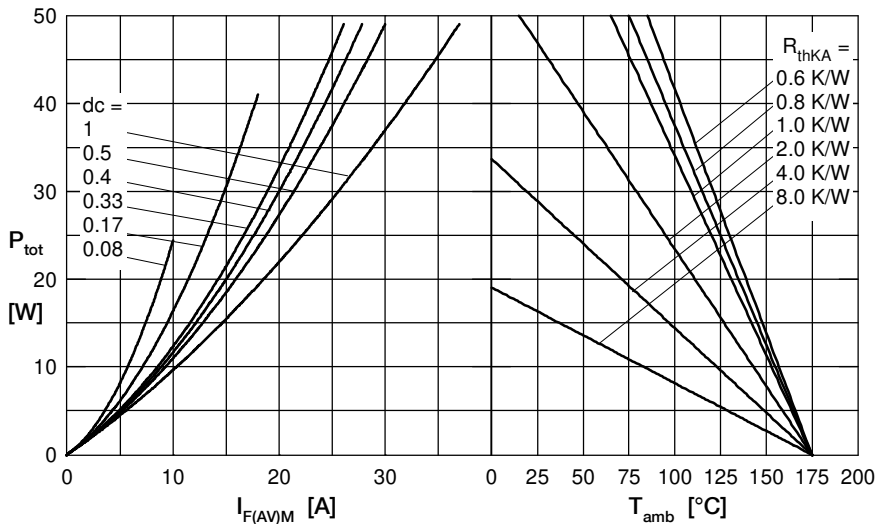

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation versus direct output current and ambient temperature

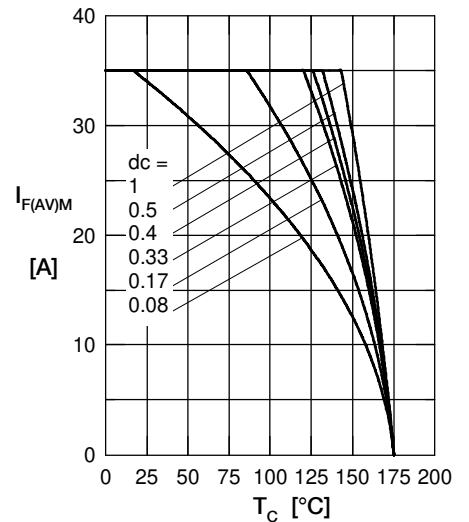


Fig. 5 Max. forward current versus case temperature

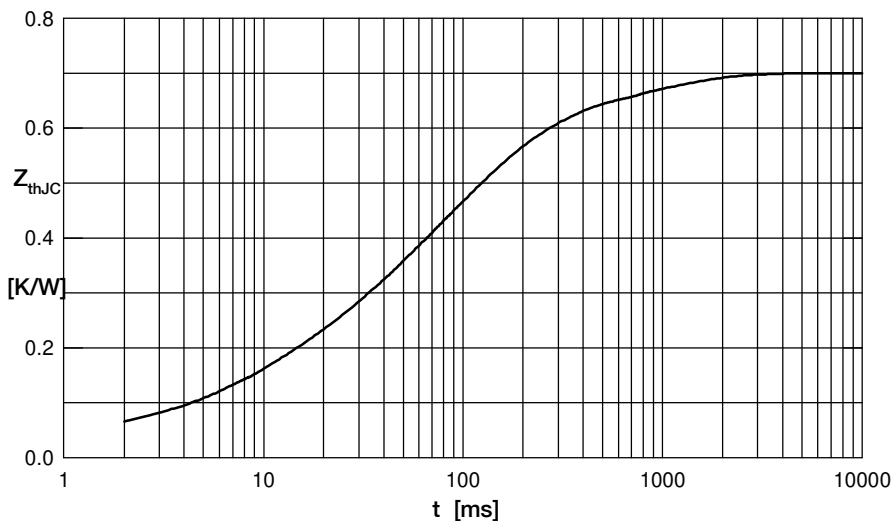


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.03	0.0003
2	0.072	0.0065
3	0.131	0.027
4	0.367	0.105
5	0.1	0.8